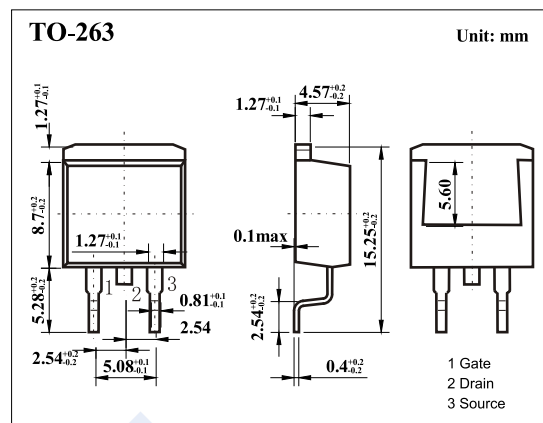
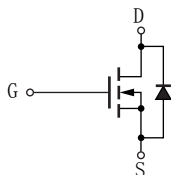


N-Channel MOSFET

2SK3269-ZJ

■ Features

- $V_{DS} = 100V$
- $I_D = 25A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 100m\Omega$ ($V_{GS} = 10V$)
- Low on-resistance, Low Q_g
- High avalanche resistance



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current	I _D	25	A
Pulsed Drain Current	I _{DM}	100	
Power Dissipation T _c = 25°C T _a = 25°C	P _D	40	W
		1.4	
Single Avalanche Energy (Note.1)	E _{AS}	22.5	mJ
Thermal Resistance.Junction- to-Ambient	R _{thJA}	89.3	°C/W
Thermal Resistance.Junction- to-Case	R _{thJC}	3.125	
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =1mA, V _{GS} =0V	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V, V _{GS} =0V			10	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =10V, I _D =1mA	2		4	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =12A			100	mΩ
Forward Transconductance	g _{FS}	V _{GS} =10V, I _D =12A	6	11		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =10V, f=1MHz		960		pF
Output Capacitance	C _{oss}			285		
Reverse Transfer Capacitance	C _{rss}			85		
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _{DS} =30V, I _D =12A, R _G =2.5Ω		15		ns
Turn-On Rise Time	t _r			10		
Turn-Off DelayTime	t _{d(off)}			65		
Turn-Off Fall Time	t _f			35		
Diode Forward Voltage	V _{SD}	I _S =15A, V _{GS} =0V			1.4	V

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Typical Characteristics

